

Flash Memory Programming Specification

1.0 DEVICE OVERVIEW

This document includes the programming specifications for the following devices:

- PIC18F13K22
 PIC18LF13K22
- PIC18F14K22
 PIC18LF14K22

2.0 PROGRAMMING OVERVIEW

The PIC18F1XK22/LF1XK22 devices can be programmed using either the high-voltage In-Circuit Serial Programming™ (ICSP™) method or the low-voltage ICSP method. Both methods can be done with the device in the users' system. The low-voltage ICSP method is slightly different than the high-voltage method and these differences are noted where applicable. The PIC18F1XK22 devices operate from 1.8 to 5.5 volts and the PIC18LF1XK22 devices operate from 1.8 to 3.6 volts. All other aspects of the PIC18F1XK22 with regards to the PIC18LF1XK22 devices are identical.

2.1 Hardware Requirements

In High-Voltage ICSP mode, the PIC18F1XK22/LF1XK22 devices require two programmable power supplies: one for VDD and one for MCLR/VPP/RA3. Both supplies should have a minimum resolution of 0.25V. Refer to Section 8.0 "AC/DC Characteristics Timing Requirements for Program/Verify Test Mode" for additional hardware parameters.

2.1.1 LOW-VOLTAGE ICSP PROGRAMMING

In Low-Voltage ICSP mode, the PIC18F1XK22/LF1XK22 devices can be programmed using a single VDD source in the operating range. The MCLR/VPP/RA3 does not have to be brought to a different voltage, but can instead be left at the normal operating voltage. Refer to Section 8.0 "AC/DC Characteristics Timing Requirements for Program/Verify Test Mode" for additional hardware parameters.

2.1.1.1 Single-Supply ICSP Programming

The LVP bit in Configuration register, CONFIG4L, enables single-supply (low-voltage) ICSP programming. The LVP bit defaults to a '1' (enabled) from the factory.

If Single-Supply Programming mode is not used, the LVP bit can be programmed to a '0' and RC3/PGM becomes a digital I/O pin. However, the LVP bit may only be programmed by entering the High-Voltage ICSP mode, where MCLR/VPP/RA3 is raised to VIHH. Once the LVP bit is programmed to a '0', only the High-Voltage ICSP mode is available and only the High-Voltage ICSP mode can be used to program the device.

- Note 1: The High-Voltage ICSP mode is always available, regardless of the state of the LVP bit, by applying VIHH to the MCLR/VPP/RA3 pin.
 - **2:** While in Low-Voltage ICSP mode, the RC3 pin can no longer be used as a general purpose I/O.

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2.2 Pin Diagrams

The pin diagrams for the PIC18F1XK22/LF1XK22 family are shown in Figure 2-1.

TABLE 2-1: PIN DESCRIPTIONS (DURING PROGRAMMING): PIC18F1XK22/LF1XK22

Pin Name	During Programming		
	Pin Name	Pin Type	Pin Description
MCLR/VPP/RA3	VPP	Р	Programming Enable
VDD(2)	VDD	Р	Power Supply
VSS ⁽²⁾	Vss	Р	Ground
RC3	PGM	I	Low-Voltage ICSP™ input when LVP Configuration bit equals '1'(1)
RA1	PGC	I	Serial Clock
RA0	PGD	I/O	Serial Data

Legend: I = Input, O = Output, P = Power

Note 1: See Figure 6-1 for more information.

2: All power supply (VDD) and ground (Vss) pins must be connected.

FIGURE 2-1: 20-PIN PDIP, SSOP AND SOIC PIN DIAGRAM FOR PIC18F1XK22/LF1XK22 20-pin PDIP, SSOP, SOIC (300 MIL) 20 □ → RA5/OSC1/CLKIN/T13CKI 19 → RA0/AN0/CVREF/VREF-/C1IN+/INT0/PGD PIC18F1XK22/LF1XK22 RA4/AN3/OSC2/CLKOUT -18 → RA1/AN1/C12IN0-/VREF+/INT1/PGC 17 ☐ ← RA2/AN2/C1OUT/T0CKI/INT2/SRQ RA3/MCLR/VPP RC5/CCP1/P1A 16 ☐ ← RC0/AN4/C2IN+ RC4/C2OUT/P1B/SRQ RC3/AN7/C12IN3-/P1C/PGM -13 ← RB4/AN10/SDI/SDA RC6/AN8/SS≺ RC7/AN9/SDO -► 🗌 RB7/TX/CK≺ 10 11 ☐ ← RB6/SCK/SCL 20-Pin QFN 4x4 RA0/AN0/CVREF/VREF-/C1IN+/INT0/PGD RA4/AN3/OSC2/CLKOUT RA5/OSC1/CLKIN/T13CKI 20 19 18 17 16 RA3/MCLR/VPP RA1/AN1/C12IN0-/VREF+/INT1/PGC 15 RC5/CCP1/P1A ◀ 2 14 RA2/AN2/C1OUT/T0CKI/INT2/SRQ PIC18F1XK22/ RC4/C2OUT/P1B/SRQ ◀ 3 13 → RC0/AN4/C2IN+ LF1XK22 RC3/AN7/C12IN3-/P1C/PGM -4 → RC1/AN5/C12IN1-12 RC6/AN8/SS-5 ← RC2/AN6/C12IN2-/P1D 11 6 7 8 9 10 RC7/AN9/SDO -RB7/TX/CK -RB6/SCK/SCL -RB5/AN11/RX/DT -RB4/AN10/SDI/SDA

3.0 MEMORY MAPS

For the PIC18F14K22/LF14K22 device, the code memory space extends from 0000h to 03FFFh (16 Kbytes) in two 8-Kbyte blocks. For the PIC18F13K22/LF13K22 device, the code memory space extends from 0000h to 01FFFh (8 Kbytes) in two 4-Kbyte blocks.

For the PIC18F14K22/LF14K22 addresses 0000h through 0FFFh, however, define a "Boot Block" region that is treated separately from Block 0. For the PIC18F13K22/LF13K22 addresses 0000h through 07FFh, define the "Boot Block" region. All of these blocks define code protection boundaries within the code memory space. The size of the Boot Block in the PIC18F14K22/LF14K22 devices can be configured as 2K, or 4 Kbyte (see Figure 3-1). The size of the Boot

Block in the PIC18F13K22/LF13K22 devices can be configured as 1K, or 2 Kbytes (see Figure 3-1). This is done through the BBSIZ bit in the Configuration register, CONFIG4L. It is important to note that increasing the size of the Block decreases the size of the Block 0.

TABLE 3-1: IMPLEMENTATION OF CODE MEMORY

Device	Code Memory Size (Bytes)
PIC18F13K22/ LF13K22	000000h-001FFFh (8K)
PIC18F14K22/ LF14K22	000000h-003FFFh (16K)

FIGURE 3-1: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18F14K22/LF14K22 DEVICES⁽¹⁾

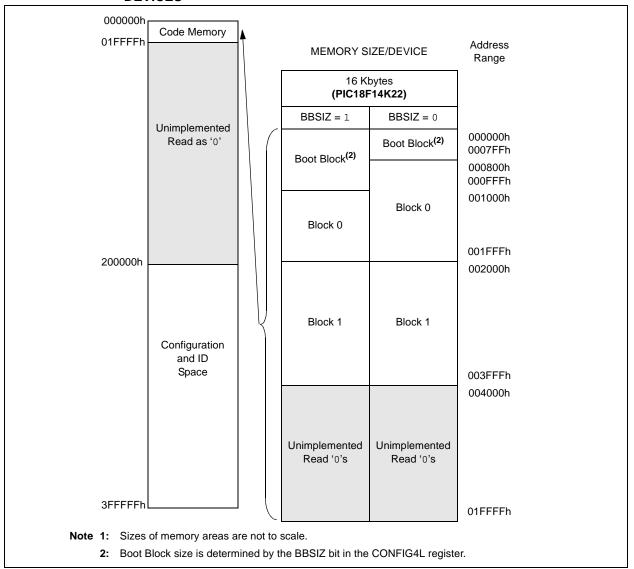
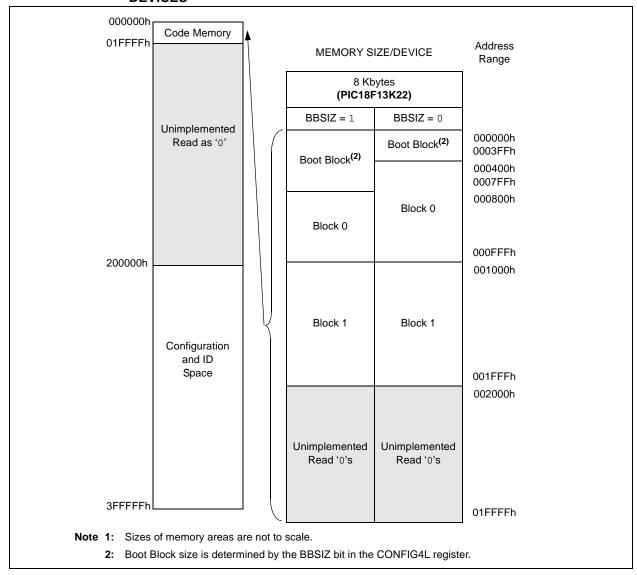


FIGURE 3-2: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18F13K22/LF13K22 DEVICES⁽¹⁾



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In addition to the code memory space, there are three blocks in the configuration and ID space that are accessible to the user through table reads and table writes. Their locations in the memory map are shown in Figure 3-3.

Users may store identification information (ID) in eight ID registers. These ID registers are mapped in addresses 200000h through 200007h. The ID locations read out normally, even after code protection is applied.

Locations 300001h through 30000Dh are reserved for the Configuration bits. These bits select various device options and are described in **Section 6.0** "**Configuration Word**". These Configuration bits read out normally, even after code protection.

Locations 3FFFFEh and 3FFFFFh are reserved for the device ID bits. These bits may be used by the programmer to identify what device type is being programmed and are described in **Section 6.0** "Configuration Word". These device ID bits read out normally, even after code protection.

3.0.1 MEMORY ADDRESS POINTER

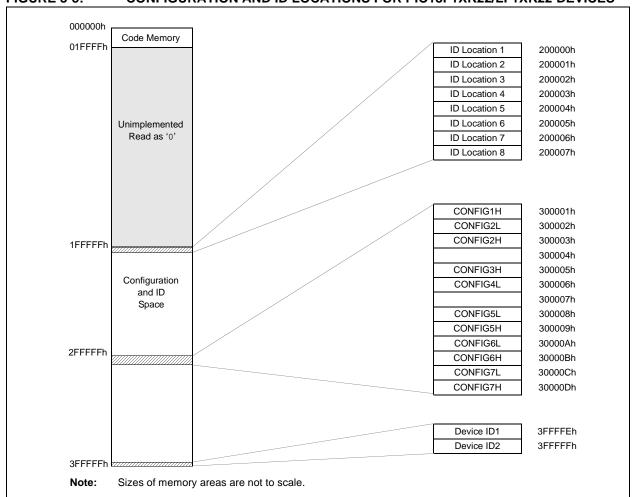
Memory in the address space, 0000000h to 3FFFFFh, is addressed via the Table Pointer register, which is comprised of three Pointer registers:

- TBLPTRU, at RAM address 0FF8h
- TBLPTRH, at RAM address 0FF7h
- · TBLPTRL, at RAM address 0FF6h

TBLPTRU	TBLPTRH	TBLPTRL
Addr[21:16]	Addr[15:8]	Addr[7:0]

The 4-bit command, '0000' (core instruction), is used to load the Table Pointer prior to using any read or write operations.

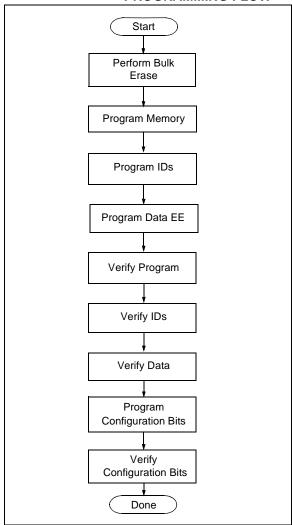
FIGURE 3-3: CONFIGURATION AND ID LOCATIONS FOR PIC18F1XK22/LF1XK22 DEVICES



3.1 High-Level Overview of the Programming Process

Figure 3-4 shows the high-level overview of the programming process. First, a Bulk Erase is performed. Next, the code memory, ID locations and data EEPROM are programmed. These memories are then verified to ensure that programming was successful. If no errors are detected, the Configuration bits are then programmed and verified.

FIGURE 3-4: HIGH-LEVEL PROGRAMMING FLOW



3.2 Entering and Exiting High-Voltage ICSP Program/Verify Mode

As shown in Figure 3-6, the High-Voltage ICSP Program/Verify mode is entered by holding PGC and PGD low and then raising MCLR/VPP/RA3 to VIHH (high voltage). Once in this mode, the code memory, data EEPROM, ID locations and Configuration bits can be accessed and programmed in serial fashion. Figure 3-7 shows the exit sequence.

The sequence that enters the device into the Program/ Verify mode places all unused I/Os in the high-impedance state.

FIGURE 3-5: VPP-FIRST PROGRAM/ VERIFY MODE ENTRY

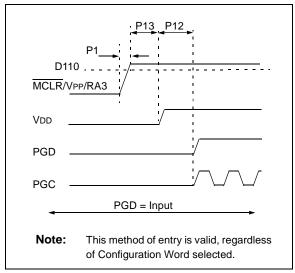
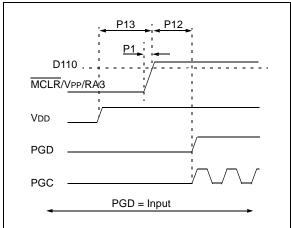
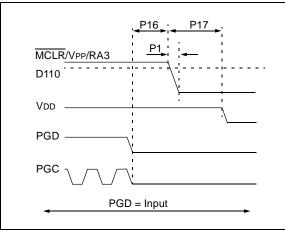


FIGURE 3-6: VDD-FIRST PROGRAM/ VERIFY MODE ENTRY



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FIGURE 3-7: EXITING HIGH-VOLTAGE PROGRAM/VERIFY MODE



3.3 Entering and Exiting Low-Voltage ICSP Program/Verify Mode

When the LVP Configuration bit is '1' (see Section 2.1.1.1 "Single-Supply ICSP Programming"), the Low-Voltage ICSP mode is enabled. As shown in Figure 3-8, Low-Voltage ICSP Program/Verify mode is entered by holding PGC and PGD low, placing a logic high on PGM and then raising MCLR/VPP/RA3 to VIH. In this mode, the RC3/PGM pin is dedicated to the programming function and ceases to be a general purpose I/O pin. Figure 3-9 shows the exit sequence.

The sequence that enters the device into the Program/ Verify mode places all unused I/Os in the high-impedance state.

FIGURE 3-8: ENTERING LOW-VOLTAGE PROGRAM/VERIFY MODE

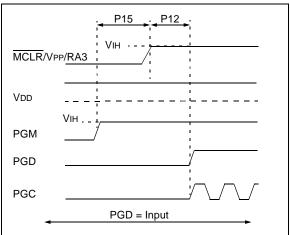
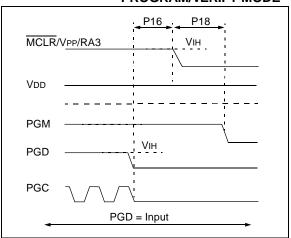


FIGURE 3-9: EXITING LOW-VOLTAGE PROGRAM/VERIFY MODE



3.4 Serial Program/Verify Operation

The PGC pin is used as a clock input pin and the PGD pin is used for entering command bits and data input/output during serial operation. Commands and data are transmitted on the rising edge of PGC, latched on the falling edge of PGC and are Least Significant bit (LSb) first.

3.4.1 4-BIT COMMANDS

All instructions are 20 bits, consisting of a leading 4-bit command followed by a 16-bit operand, which depends on the type of command being executed. To input a command, PGC is cycled four times. The commands needed for programming and verification are shown in Table 3-2.

Depending on the 4-bit command, the 16-bit operand represents 16 bits of input data or 8 bits of input data and 8 bits of output data.

Throughout this specification, commands and data are presented as illustrated in Table 3-3. The 4-bit command, Most Significant bit (MSb), is shown first. The command operand, or "Data Payload", is shown <MSB><LSB>. Figure 3-10 demonstrates how to serially present a 20-bit command/operand to the device.

3.4.2 CORE INSTRUCTION

The core instruction passes a 16-bit instruction to the CPU core for execution. This is needed to set up registers as appropriate for use with other commands.

TABLE 3-2: COMMANDS FOR PROGRAMMING

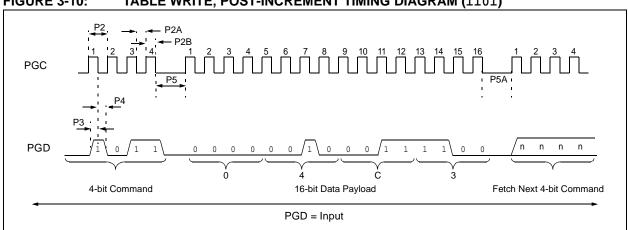
Description	4-Bit Command
Core Instruction (Shift in16-bit instruction)	0000
Shift out TABLAT register	0010
Table Read	1000
Table Read, post-increment	1001
Table Read, post-decrement	1010
Table Read, pre-increment	1011
Table Write	1100
Table Write, post-increment by 2	1101
Table Write, start programming, post-increment by 2	1110
Table Write, start programming	1111

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TABLE 3-3: SAMPLE COMMAND SEQUENCE

4-Bit Command	Data Payload	Core Instruction
1101	3C 40	Table Write, post-increment by 2

FIGURE 3-10: TABLE WRITE, POST-INCREMENT TIMING DIAGRAM (1101)



4.0 DEVICE PROGRAMMING

Programming includes the ability to erase or write the various memory regions within the device.

In all cases, except high-voltage ICSP Bulk Erase, the EECON1 register must be configured in order to operate on a particular memory region.

When using the EECON1 register to act on code memory, the EEPGD bit must be set (EECON1<7>= 1) and the CFGS bit must be cleared (EECON1<6>= 0). The WREN bit must be set (EECON1<2>= 1) to enable writes of any sort (e.g., erases) and this must be done prior to initiating a write sequence. The FREE bit must be set (EECON1<4>= 1) in order to erase the program space being pointed to by the Table Pointer. The erase or write sequence is initiated by setting the WR bit (EECON1<1>= 1). It is strongly recommended that the WREN bit only be set immediately prior to a program or erase.

4.1 ICSP Erase

4.1.1 HIGH-VOLTAGE ICSP BULK ERASE

Erasing code or data EEPROM is accomplished by configuring two Bulk Erase Control registers located at 3C0004h and 3C0005h. Code memory may be erased portions at a time, or the user may erase the entire device in one action. Bulk Erase operations will also clear any code-protect settings associated with the memory block erased. Erase options are detailed in Table 4-1. If data EEPROM is code-protected (CPD = 0), the user must request an erase of data EEPROM (e.g., 00008484h as shown in Table 4-1).

TABLE 4-1: BULK ERASE OPTIONS

Description	Data (3C0005h:3C0004h)
Chip Erase	0F0F8787h
Erase Data EEPROM	00008484h
Erase Boot Block	00008181h
Erase Config Bits	00008282h
Erase Code EEPROM Block 0	01018080h
Erase Code EEPROM Block 1	02028080h
Erase Code EEPROM Block 2	04048080h
Erase Code EEPROM Block 3	08088080h

The actual Bulk Erase function is a self-timed operation. Once the erase has started (falling edge of the 4th PGC after the NOP command), serial execution will cease until the erase completes (parameter P11). During this time, PGC may continue to toggle but PGD must be held low.

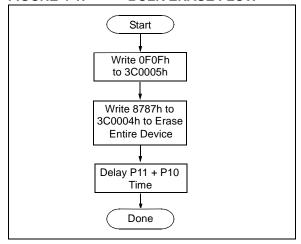
The code sequence to erase the entire device is shown in Table 4-2 and the flowchart is shown in Figure 4-1.

Note: A Bulk Erase is the only way to reprogram code-protect bits from an "on" state to an "off" state.

TABLE 4-2: BULK ERASE COMMAND SEQUENCE

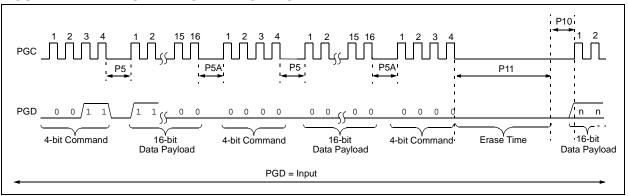
4-Bit Command	Data Payload	Core Instruction
0000	0E 3C	MOVLW 3Ch
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPTRH
0000	0E 05	MOVLW 05h
0000	6E F6	MOVWF TBLPTRL
1100	0F 0F	Write OFh to 3C0005h
0000	0E 3C	MOVLW 3Ch
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPTRH
0000	0E 04	MOVLW 04h
0000	6E F6	MOVWF TBLPTRL
1100	87 87	Write 8787h TO 3C0004h to erase entire device.
0000	00 00	NOP
0000	00 00	Hold PGD low until erase completes.

FIGURE 4-1: BULK ERASE FLOW



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4.1.2 LOW-VOLTAGE ICSP BULK ERASE

When using low-voltage ICSP, the part must be supplied by the voltage specified in parameter D111 if a Bulk Erase is to be executed. All other Bulk Erase details as described above apply.

If it is determined that a program memory erase must be performed at a supply voltage below the Bulk Erase limit, refer to the erase methodology described in Section 4.1.3 "ICSP Row Erase" and Section 4.2.1 "Modifying Code Memory".

If it is determined that a data EEPROM erase must be performed at a supply voltage below the Bulk Erase limit, follow the methodology described in **Section 4.3** "Data EEPROM Programming" and write '1's to the array.

4.1.3 ICSP ROW ERASE

Regardless of whether high or low-voltage ICSP is used, it is possible to erase one row (64 bytes of data), provided the block is not code or write-protected. Rows are located at static boundaries beginning at program memory address 000000h, extending to the internal program memory limit (see **Section 3.0 "Memory Maps"**).

The Row Erase duration is self-timed. After the WR bit in EECON1 is set, two NOPs are issued. Erase starts upon the 4th PGC of the second NOP. It ends when the WR bit is cleared by hardware.

The code sequence to Row Erase a PIC18F1XK22/LF1XK22 device is shown in Table 4-3. The flowchart shown in Figure 4-3 depicts the logic necessary to completely erase the PIC18F1XK22/LF1XK22 devices. The timing diagram for Row Erase is identical to the data EEPROM write timing shown in Figure 4-7.

Note: The TBLPTR register can point at any byte within the row intended for erase.

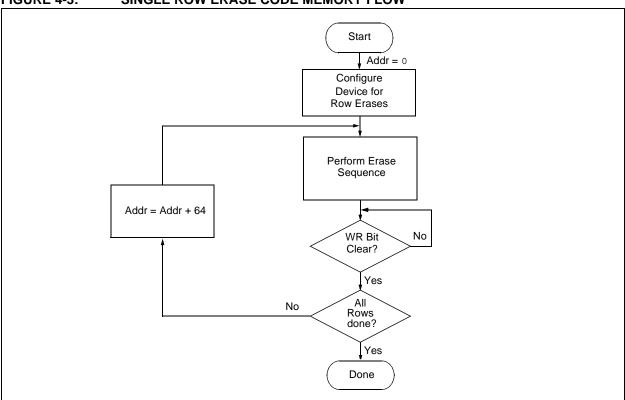
TABLE 4-3: ERASE CODE MEMORY CODE SEQUENCE

4-bit Command	Data Payload	Core Instruction	
Step 1: Direct a	ccess to code memor	ry and enable writes.	
0000	8E A6	BSF EECON1, EEPGD	
0000	9C A6 84 A6	BCF EECON1, CFGS BSF EECON1, WREN	
Step 2: Point to	first row in code men	nory.	
0000	6A F8	CLRF TBLPTRU	
0000	6A F7 6A F6	CLRF TBLPTRL	
Step 3: Enable	Step 3: Enable erase and erase single row.		
0000	88 A6	BSF EECON1, FREE	
0000	82 A6	BSF EECON1, WR	
0000	00 00	NOP	
0000	00 00	NOP Erase starts on the 4th clock of this instruction	
Step 4: Poll WR	bit. Repeat until bit is	s clear.	
0000	50 A6	MOVF EECON1, W, 0	
0000	6E F5	MOVWF TABLAT	
0000	00 00	NOP	
0010	<msb><lsb></lsb></msb>	Shift out data ⁽¹⁾	
Step 5: Hold PG	Step 5: Hold PGC low for time P10.		
Step 6: Repeat	Step 6: Repeat step 3 with Address Pointer incremented by 64 until all rows are erased.		
Step 7: Disable	Step 7: Disable writes.		
0000	94 A6	BCF EECON1, WREN	

Note 1: See Figure 5-4 for details on shift out data timing.

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FIGURE 4-3: SINGLE ROW ERASE CODE MEMORY FLOW



4.2 Code Memory Programming

Programming code memory is accomplished by first loading data into the write buffer and then initiating a programming sequence. The write and erase buffer sizes shown in Table 4-4 can be mapped to any location of the same size beginning at 000000h. The actual memory write sequence takes the contents of this buffer and programs the proper amount of code memory that contains the Table Pointer.

The programming duration is externally timed and is controlled by PGC. After a Start Programming command is issued (4-bit command, '1111'), a NOP is issued, where the 4th PGC is held high for the duration of the programming time, P9.

After PGC is brought low, the programming sequence is terminated. PGC must be held low for the time specified by parameter P10 to allow high-voltage discharge of the memory array.

The code sequence to program a PIC18F1XK22/LF1XK22 device is shown in Table 4-5. The flowchart shown in Figure 4-4 depicts the logic necessary to completely write a PIC18F1XK22/LF1XK22 device. The timing diagram that details the Start Programming command and parameters P9 and P10 is shown in Figure 4-5.

Note: The TBLPTR register must point to the same region when initiating the programming sequence as it did when the write buffers were loaded.

TABLE 4-4: WRITE AND ERASE BUFFER SIZES

Devices	Write Buffer Size (bytes)	Erase Size (bytes)
PIC18F14K22	16	64
PIC18F13K22	8	64

TABLE 4-5: WRITE CODE MEMORY CODE SEQUENCE

IABLE 4-3.	WATTE CODE MEMORT CODE SEQUENCE		
4-bit Command	Data Payload	Core Instruction	
Step 1: Direct a	ccess to code memor	ry.	
0000 0000 0000	8E A6 9C A6 84 A6	BSF EECON1, EEPGD BCF EECON1, CFGS BSF EECON1, WREN	
Step 2: Point to	row to write.		
0000 0000 0000 0000 0000	0E <addr[21:16]> 6E F8 0E <addr[15:8]> 6E F7 0E <addr[7:0]> 6E F6</addr[7:0]></addr[15:8]></addr[21:16]>	MOVLW <addr[21:16]> MOVWF TBLPTRU MOVLW <addr[15:8]> MOVWF TBLPTRH MOVLW <addr[7:0]> MOVWF TBLPTRL</addr[7:0]></addr[15:8]></addr[21:16]>	
Step 3: Load wi	Step 3: Load write buffer. Repeat for all but the last two bytes.		
1101	<msb><lsb></lsb></msb>	Write 2 bytes and post-increment address by 2.	
Step 4: Load wi	Step 4: Load write buffer for last two bytes and start programming.		
1111 0000	<msb><lsb> 00 00</lsb></msb>	Write 2 bytes and start programming. NOP - hold PGC high for time P9 and low for time P10.	
To continue writing data, repeat steps 2 through 4, where the Address Pointer is incremented by 2 at each iteration of the loop.			

FIGURE 4-4: PROGRAM CODE MEMORY FLOW

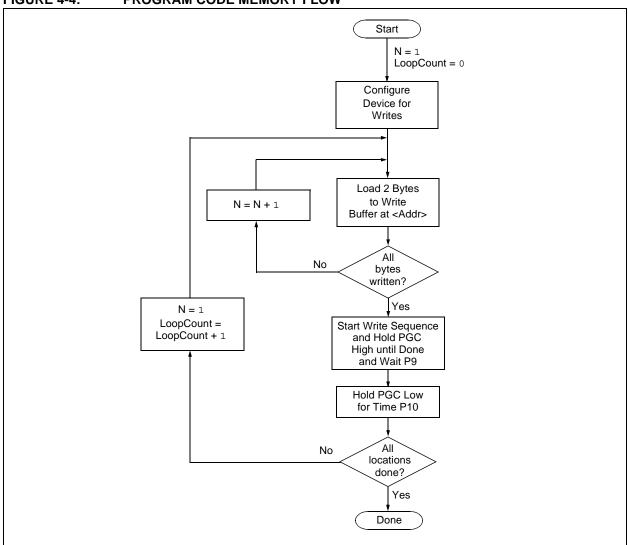
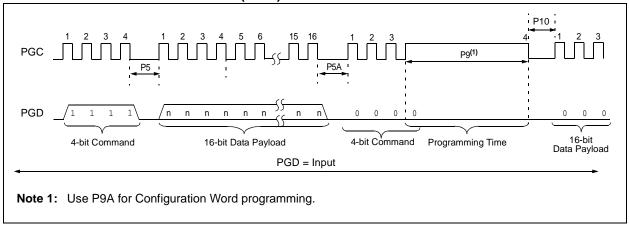


FIGURE 4-5: TABLE WRITE AND START PROGRAMMING INSTRUCTION TIMING DIAGRAM (1111)



4.2.1 MODIFYING CODE MEMORY

The previous programming example assumed that the device has been Bulk Erased prior to programming (see **Section 4.1.1 "High-Voltage ICSP Bulk Erase"**). It may be the case, however, that the user wishes to modify only a section of an already programmed device.

The appropriate number of bytes required for the erase buffer must be read out of code memory (as described in **Section 5.2 "Verify Code Memory and ID Locations"**) and buffered. Modifications can be made on this buffer. Then, the block of code memory that was read out must be erased and rewritten with the modified data.

The WREN bit must be set if the WR bit in EECON1 is used to initiate a write sequence.

TABLE 4-6: MODIFYING CODE MEMORY

4-bit Command	Data Payload	Core Instruction
Step 1: Direct acc	cess to code memory.	ı
0000	8E A6	BSF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
Step 2: Read cod	le memory into buffer (Secti	on 5.1 "Read Code Memory, ID Locations and Configuration Bits").
Step 3: Set the Ta	able Pointer for the block to	be erased.
0000	0E <addr[21:16]></addr[21:16]>	MOVLW <addr[21:16]></addr[21:16]>
0000	6E F8	MOVWF TBLPTRU
0000	0E <addr[8:15]></addr[8:15]>	MOVLW <addr[8:15]></addr[8:15]>
0000	6E F7	MOVWF TBLPTRH
0000	0E <addr[7:0]></addr[7:0]>	MOVLW <addr[7:0]></addr[7:0]>
0000	6E F6	MOVWF TBLPTRL
Step 4: Enable m	emory writes and setup an	erase.
0000	84 A6	BSF EECON1, WREN
0000	88 A6	BSF EECON1, FREE
Step 5: Initiate era	ase.	
0000	88 A6	BSF EECON1, FREE
0000	82 A6	BSF EECON1, WR
0000	00 00	NOP
0000	00 00	NOP Erase starts on the 4th clock of this instruction
Step 6: Poll WR b	oit. Repeat until bit is clear.	
0000	50 A6	MOVF EECON1, W, 0
0000	6E F5	MOVWF TABLAT
0000	00 00	NOP
0000	<msb><lsb></lsb></msb>	Shift out data ⁽¹⁾
Step 7: Load write	e buffer. The correct bytes w	vill be selected based on the Table Pointer.
0000	0E <addr[21:16]></addr[21:16]>	MOVLW <addr[21:16]></addr[21:16]>
0000	6E F8	MOVWF TBLPTRU
0000	0E <addr[8:15]></addr[8:15]>	MOVLW <addr[8:15]></addr[8:15]>
0000	6E F7	MOVWF TBLPTRH
0000	0E <addr[7:0]></addr[7:0]>	MOVLW <addr[7:0]></addr[7:0]>
0000	6E F6	MOVWF TBLPTRL
1101	<msb><lsb></lsb></msb>	Write 2 bytes and post-increment address by 2.
•	•	
•	•	Repeat as many times as necessary to fill the write buffer
•	MCD. J.CD:	Write 2 bytes and start programming.
1111 0000	<msb><lsb> 00 00</lsb></msb>	NOP - hold PGC high for time P9 and low for time P10.
		rough 6 whore the Address Deinter is ingremented by the consequents as a first and
		rough 6, where the Address Pointer is incremented by the appropriate number of bytes he write cycle must be repeated enough times to completely rewrite the contents of the
Step 8: Disable w	vrites.	
0000	94 A6	BCF EECON1, WREN
0000	0 1 / 10	201 2200H1, HILLI

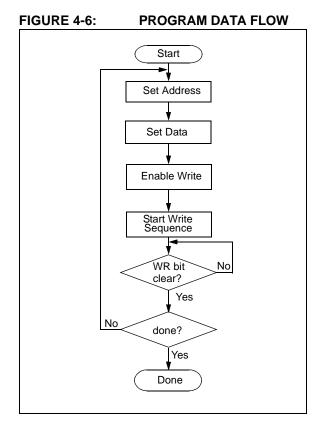
4.3 Data EEPROM Programming

Data EEPROM is accessed one byte at a time via an Address Pointer (register EEADR) and a data latch (EEDATA). Data EEPROM is written by loading EEADR with the desired memory location, EEDATA with the data to be written and initiating a memory write by appropriately configuring the EECON1 register. A byte write automatically erases the location and writes the new data (erase-before-write).

When using the EECON1 register to perform a data EEPROM write, both the EEPGD and CFGS bits must be cleared (EECON1<7:6> = 00). The WREN bit must be set (EECON1<2> = 1) to enable writes of any sort and this must be done prior to initiating a write sequence. The write sequence is initiated by setting the WR bit (EECON1<1> = 1).

The write begins on the falling edge of the 24th PGC after the WR bit is set. It ends when the WR bit is cleared by hardware.

After the programming sequence terminates, PGC must be held low for the time specified by parameter P10 to allow high-voltage discharge of the memory array.



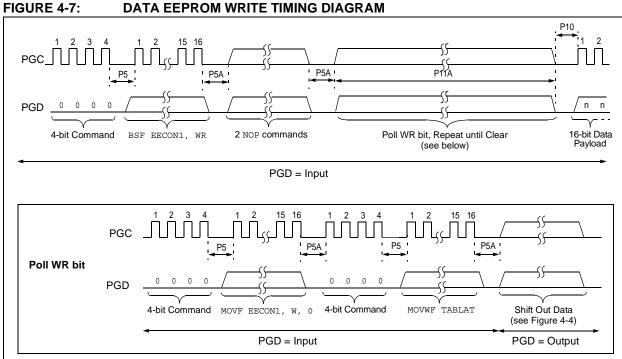


TABLE 4-7: PROGRAMMING DATA MEMORY

4-bit Command	Data Payload	Core Instruction	
Step 1: Direct ad	ccess to data EEPROM.		
0000	9E A6 9C A6	BCF EECON1, EEPGD BCF EECON1, CFGS	
Step 2: Set the	data EEPROM Address I	Pointer.	
0000 0000	0E <addr> 6E A9</addr>	MOVLW <addr> MOVWF EEADR</addr>	
Step 3: Load the	data to be written.		
0000 0000	0E <data> 6E A8</data>	MOVLW <data> MOVWF EEDATA</data>	
Step 4: Enable r	memory writes.		
0000	84 A6	BSF EECON1, WREN	
Step 5: Initiate w	rite.		
0000 0000 0000	82 A6 00 00 00 00	BSF EECON1, WR NOP NOP; write starts on 4th clock of this instruction	
Step 6: Poll WR	bit, repeat until the bit is	clear.	
0000 0000 0000 0010	50 A6 6E F5 00 00 <msb><lsb></lsb></msb>	MOVF EECON1, W, 0 MOVWF TABLAT NOP Shift out data(1)	
Step 7: Hold PG	Step 7: Hold PGC low for time P10.		
Step 8: Disable	writes.		
0000	94 A6	BCF EECON1, WREN	
Repeat steps 2 through 8 to write more data.			

Note 1: See Figure 5-4 for details on shift out data timing.

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4.4 ID Location Programming

The ID locations are programmed much like the code memory. The ID registers are mapped in addresses 200000h through 200007h. These locations read out normally even after code protection.

Note: The user only needs to fill the first 8 bytes of the write buffer in order to write the ID locations.

Table 4-8 demonstrates the code sequence required to write the ID locations.

In order to modify the ID locations, refer to the methodology described in **Section 4.2.1 "Modifying Code Memory**". As with code memory, the ID locations must be erased before being modified.

TABLE 4-8: WRITE ID SEQUENCE

4-bit Command	Data Payload	Core Instruction
Step 1: Direct ad	ccess to code memory.	
0000	8E A6	BSF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
0000	84 A6	BSF EECON1, WREN
Step 2: Set Tabl	e Pointer to ID. Load writ	te buffer with 8 bytes and write.
0000	0E 20	MOVLW 20h
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPTRH
0000	0E 00	MOVLW 00h
0000	6E F6	MOVWF TBLPTRL
1101	<msb><lsb></lsb></msb>	Write 2 bytes and post-increment address by 2.
1101	<msb><lsb></lsb></msb>	Write 2 bytes and post-increment address by 2.
1101	<msb><lsb></lsb></msb>	Write 2 bytes and post-increment address by 2.
1111	<msb><lsb></lsb></msb>	Write 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9 and low for time P10.

4.5 Boot Block Programming

The code sequence detailed in Table 4-5 should be used, except that the address used in "Step 2" will be in the following ranges:

If BBSIZ = 0:

000000h-0003FFh for PIC18F13K22/LF13K22 000000h-0007FFh for PIC18F14K22/LF14K22

If BBSIZ = 1:

000000h-0007FFh for PIC18F13K22/LF13K22 000000h-000FFFh for PIC18F14K22/LF14K22

4.6 Configuration Bits Programming

Unlike code memory, the Configuration bits are programmed a byte at a time. The Table Write, Begin Programming 4-bit command ('1111') is used, but only 8 bits of the following 16-bit payload will be written. The LSB of the payload will be written to even addresses and the MSB will be written to odd addresses. The code sequence to program two consecutive configuration locations is shown in Table 4-9. See Figure 4-5 for the timing diagram.

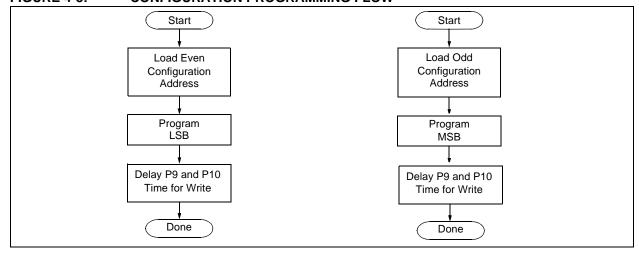
Note: The address must be explicitly written for each byte programmed. The addresses can not be incremented in this mode.

TABLE 4-9: SET ADDRESS POINTER TO CONFIGURATION LOCATION

4-bit Command	Data Payload	Core Instruction
Step 1: Direct a	ccess to configuration me	emory.
0000	8E A6	BSF EECON1, EEPGD
0000	8C A6	BSF EECON1, CFGS
0000	84 A6	BSF EECON1, WREN
Step 2 ⁽¹⁾ : Set Ta	able Pointer for configura	tion byte to be written. Write even/odd addresses.
0000	0E 30	MOVLW 30h
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPRTH
0000	0E 00	MOVLW 00h
0000	6E F6	MOVWF TBLPTRL
1111	<msb ignored=""><lsb></lsb></msb>	Load 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9 and low for time P10.
0000	0E 01	MOVLW 01h
0000	6E F6	MOVWF TBLPTRL
1111	<msb><lsb ignored=""></lsb></msb>	Load 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9A and low for time P10.

Note 1: Enabling the write protection of Configuration bits (WRTC = 0 in CONFIG6H) will prevent further writing of Configuration bits. Always write all the Configuration bits before enabling the write protection for Configuration bits.

FIGURE 4-8: CONFIGURATION PROGRAMMING FLOW



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5.0 READING THE DEVICE

5.1 Read Code Memory, ID Locations and Configuration Bits

Code memory is accessed one byte at a time via the 4-bit command, '1001' (table read, post-increment). The contents of memory pointed to by the Table Pointer (TBLPTRU:TBLPTRH:TBLPTRL) are serially output on PGD.

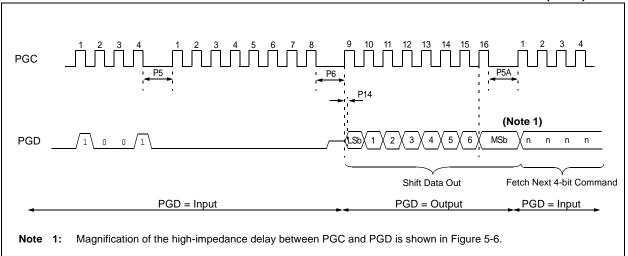
The 4-bit command is shifted in LSb first. The read is executed during the next 8 clocks, then shifted out on PGD during the last 8 clocks, LSb to MSb. A delay of P6 must be introduced after the falling edge of the 8th PGC of the operand to allow PGD to transition from an input to an output. During this time, PGC must be held low (see Figure 5-1). This operation also increments the Table Pointer by one, pointing to the next byte in code memory for the next read.

This technique will work to read any memory in the 000000h to 3FFFFFh address space, so it also applies to the reading of the ID and Configuration registers.

TABLE 5-1: READ CODE MEMORY SEQUENCE

4-bit Command	Data Payload	Core Instruction			
Step 1: Set Tabl	e Pointer				
0000	0E <addr[21:16]></addr[21:16]>	MOVLW Addr[21:16]			
0000	6E F8	MOVWF TBLPTRU			
0000	0E <addr[15:8]></addr[15:8]>	MOVLW <addr[15:8]></addr[15:8]>			
0000	6E F7	MOVWF TBLPTRH			
0000	0E <addr[7:0]></addr[7:0]>	MOVLW <addr[7:0]></addr[7:0]>			
0000	6E F6	MOVWF TBLPTRL			
Step 2: Read memory and then shift out on PGD, LSb to MSb					
1001	00 00	TBLRD *+			



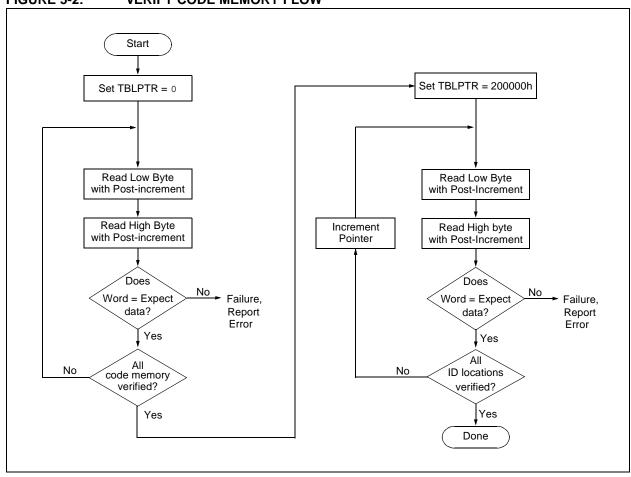


5.2 Verify Code Memory and ID Locations

The verify step involves reading back the code memory space and comparing it against the copy held in the programmer's buffer. Memory reads occur a single byte at a time, so two bytes must be read to compare against the word in the programmer's buffer. Refer to Section 5.1 "Read Code Memory, ID Locations and Configuration Bits" for implementation details of reading code memory.

The Table Pointer must be manually set to 200000h (base address of the ID locations) once the code memory has been verified. The post-increment feature of the table read 4-bit command can not be used to increment the Table Pointer beyond the code memory space. In a 64-Kbyte device, for example, a post-increment read of address FFFFh will wrap the Table Pointer back to 000000h, rather than point to unimplemented address, 010000h.

FIGURE 5-2: VERIFY CODE MEMORY FLOW



5.3 Verify Configuration Bits

A configuration address may be read and output on PGD via the 4-bit command, '1001'. Configuration data is read and written in a byte-wise fashion, so it is not necessary to merge two bytes into a word prior to a compare. The result may then be immediately compared to the appropriate configuration data in the programmer's memory for verification. Refer to Section 5.1 "Read Code Memory, ID Locations and Configuration Bits" for implementation details of reading configuration data.

5.4 Read Data EEPROM Memory

Data EEPROM is accessed one byte at a time via an Address Pointer (register EEADR) and a data latch (EEDATA). Data EEPROM is read by loading EEADR with the desired memory location and initiating a memory read by appropriately configuring the EECON1 register. The data will be loaded into EEDATA, where it may be serially output on PGD via the 4-bit command, '0010' (Shift Out Data Holding register). A delay of P6 must be introduced after the falling edge of the 8th PGC of the operand to allow PGD to transition from an input to an output. During this time, PGC must be held low (see Figure 5-4).

The command sequence to read a single byte of data is shown in Table 5-2.

FIGURE 5-3: READ DATA EEPROM FLOW

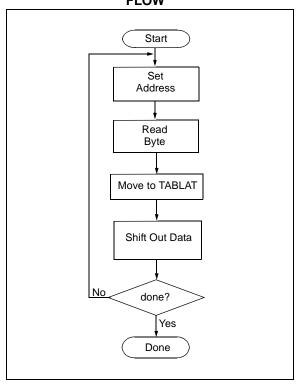
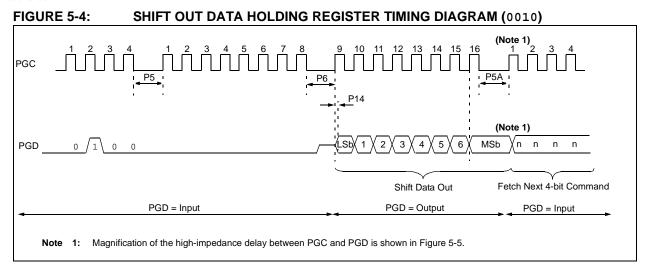


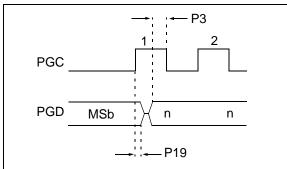
TABLE 5-2: READ DATA EEPROM MEMORY

4-bit Command	Data Payload	Core Instruction
Step 1: Direct acc	ess to data EEPROM.	
0000	9E A6 9C A6	BCF EECON1, EEPGD BCF EECON1, CFGS
Step 2: Set the da	ata EEPROM Address Point	er.
0000	0E <addr> 6E A9</addr>	MOVLW <addr> MOVWF EEADR</addr>
Step 3: Initiate a n	memory read.	
0000	80 A6	BSF EECON1, RD
Step 4: Load data	into the Serial Data Holding	g register.
0000 0000 0000 0010	50 A8 6E F5 00 00 <msb><lsb></lsb></msb>	MOVF EEDATA, W, 0 MOVWF TABLAT NOP Shift Out Data(1)

Note 1: The <LSB> is undefined. The <MSB> is the data.







5.5 Verify Data EEPROM

A data EEPROM address may be read via a sequence of core instructions (4-bit command, '0000') and then output on PGD via the 4-bit command, '0010' (TABLAT register). The result may then be immediately compared to the appropriate data in the programmer's memory for verification. Refer to **Section 5.4 "Read Data EEPROM Memory"** for implementation details of reading data EEPROM.

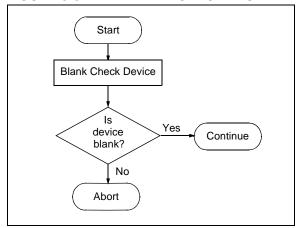
5.6 Blank Check

The term "Blank Check" means to verify that the device has no programmed memory cells. All memories must be verified: code memory, data EEPROM, ID locations and Configuration bits. The device ID registers (3FFFFEh:3FFFFFh) should be ignored.

A "blank" or "erased" memory cell will read as a '1'. Therefore, Blank Checking a device merely means to verify that all bytes read as FFh except the Configuration bits. Unused (reserved) Configuration bits will read '0' (programmed). Refer to Table 6-1 for blank configuration expect data for the various PIC18F1XK22/LF1XK22 devices.

Given that Blank Checking is merely code and data EEPROM verification with FFh expect data, refer to Section 5.4 "Read Data EEPROM Memory" and Section 5.2 "Verify Code Memory and ID Locations" for implementation details.

FIGURE 5-6: BLANK CHECK FLOW



6.0 CONFIGURATION WORD

The PIC18F1XK22/LF1XK22 devices have several Configuration Words. These bits can be set or cleared to select various device configurations. All other memory areas should be programmed and verified prior to setting Configuration Words. These bits may be read out normally, even after read or code protection. See Table 6-1 for a list of Configuration bits and device IDs and Table 6-3 for the Configuration bit descriptions.

6.1 ID Locations

A user may store identification information (ID) in eight ID locations mapped in 200000h:200007h. It is recommended that the Most Significant nibble of each ID be Fh. In doing so, if the user code inadvertently tries to execute from the ID space, the ID data will execute as a NOP.

6.2 Device ID Word

The device ID word for the PIC18F1XK22/LF1XK22 devices is located at 3FFFFEh:3FFFFh. These bits may be used by the programmer to identify what device type is being programmed and read out normally, even after code or read protection. See Table 6-2 for a complete list of device ID values.

FIGURE 6-1: READ DEVICE ID WORD FLOW

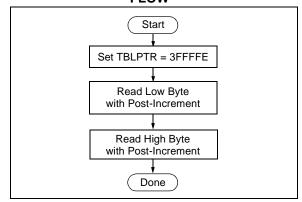


TABLE 6-1: CONFIGURATION BITS AND DEVICE IDs

File	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Default/ Unprogrammed Value
300001h	CONFIG1H	IESO	FCMEN	PRI_CLK_EN	PLL_EN	FOSC3	FOSC2	FOSC1	FOSC0	0010 0111
300002h	CONFIG2L	_	-	_	BORV1	BORV0	BOREN1	BOREN0	PWRTEN	1 1111
300003h	CONFIG2H	_	-	_	WDPS3	WDPS2	WDPS1	WDPS0	WDTEN	1 1111
300005h	CONFIG3H	MCLRE	-	_	_	HFOFST	_	_	_	1 1
300006h	CONFIG4L	BKBUG	ENHCPU	_	_	BBSIZ	LVP	_	STVREN	10 01-1
300008h	CONFIG5L	_	_	_	_	_	_	CP1	CP0	11
300009h	CONFIG5H	CPD	СРВ	_	_	_	_	_	_	11
30000Ah	CONFIG6L	_	_	_	_	_	_	WRT1	WRT0	11
30000Bh	CONFIG6H	WRTD	WRTB	WRTC	_	_	_	_	_	111
30000Ch	CONFIG7L	_	_	_	_	_	_	EBTR1	EBTR0	11
30000Dh	CONFIG7H	_	EBTRB	_	_	_	_	_	_	-1
3FFFFEh	DEVID1 ⁽²⁾	DEV2	DEV1	DEV0	REV4	REV3	REV2	REV1	REV0	See Table 6-2
3FFFFFh	DEVID2 ⁽²⁾	DEV10	DEV9	DEV8	DEV7	DEV6	DEV5	DEV4	DEV3	See Table 6-2

Legend: x = unknown, u = unchanged, - = unimplemented. Shaded cells are unimplemented, read as '0'.

Note 1: These bits are only implemented on specific devices. Refer to **Section 3.0 "Memory Maps"** to determine which bits apply based on available memory.

^{2:} DEVID registers are read-only and cannot be programmed by the user.

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TABLE 6-2: DEVICE ID VALUE

Device	Device ID Value				
Device	DEVID2	DEVID1			
PIC18LF13K22	4Fh	100x xxxx			
PIC18LF14K22	4Fh	011x xxxx			
PIC18F13K22	4Fh	010x xxxx			
PIC18F14K22	4Fh	001x xxxx			

Note: The 'x's in DEVID1 contain the device revision code.

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TABLE 6-3: PIC18F1XK22/LF1XK22 BIT DESCRIPTIONS

Bit Name	Configuration Words	Description
IESO	CONFIG1H	Internal External Switchover bit 1 = Internal External Switchover mode enabled 0 = Internal External Switchover mode disabled
FCMEN	CONFIG1H	Fail-Safe Clock Monitor Enable bit 1 = Fail-Safe Clock Monitor enabled 0 = Fail-Safe Clock Monitor disabled
PRI_CLK_EN	CONFIG1H	Primary Clock Enable bit 1 = Primary Clock enabled 0 = Primary Clock disabled
PLL_EN	CONFIG1H	4 X PLL Enable bit 1 = Oscillator multiplied by 4 0 = Oscillator used directly
FOSC<3:0>	CONFIG1H	Oscillator Selection bits 1111 = External RC oscillator, CLKOUT function on OSC2 1110 = External RC oscillator, CLKOUT function on OSC2 1101 = EC oscillator (low) 1100 = EC oscillator, CLKOUT function on OSC2 (low) 1011 = EC oscillator (medium) 1010 = EC oscillator, CLKOUT function on OSC2 (medium) 1001 = Internal RC oscillator, CLKOUT function on OSC2 1000 = Internal RC oscillator 0111 = External RC oscillator 0110 = External RC oscillator, CLKOUT function on OSC2 0101 = EC oscillator (high) 0100 = EC oscillator, CLKOUT function on OSC2 (high) 0011 = External RC oscillator, CLKOUT function on OSC2 0010 = HS oscillator 0001 = XT oscillator 0000 = LP oscillator
BORV<1:0>	CONFIG2L	Brown-out Reset Voltage bits 11 = VBOR set to 1.9V 10 = VBOR set to 2.2V 01 = VBOR set to 2.7V 00 = VBOR set to 3.0V
BOREN<1:0>	CONFIG2L	Brown-out Reset Enable bits 11 = Brown-out Reset enabled in hardware only (SBOREN is disabled) 10 = Brown-out Reset enabled in hardware only and disabled in Sleep mode SBOREN is disabled) 01 = Brown-out Reset enabled and controlled by software (SBOREN is enabled) 00 = Brown-out Reset disabled in hardware and software
PWRTEN	CONFIG2L	Power-up Timer Enable bit 1 = PWRT disabled 0 = PWRT enabled

TABLE 6-3: PIC18F1XK22/LF1XK22 BIT DESCRIPTIONS (CONTINUED)

Bit Name	Configuration Words	Description
WDPS<3:0>	CONFIG2H	Watchdog Timer Postscaler Select bits
		1111 = 1:32,768
		1110 = 1:16,384
		1101 = 1:8,192
		1100 = 1:4,096
		1011 = 1:2,048
		1010 = 1:1,024
		1001 = 1:512
		1000 = 1:256 0111 = 1:128
		0110 = 1:64
		0101 = 1:32
		0100 = 1:16
		0011 = 1:8
		0010 = 1:4
		0001 = 1:2
		0000 = 1:1
WDTEN	CONFIG2H	Watchdog Timer Enable bit
		1 = WDT enabled
		0 = WDT disabled (control is placed on SWDTEN bit)
MCLRE	CONFIG3H	MCLR Pin Enable bit
		$1 = \overline{MCLR}$ pin enabled, RA3 input pin disabled
		0 = RA3 input pin enabled, MCLR pin disabled
HFOFST	CONFIG3H	HFINTOSC Fast Start
		1 = HFINTOSC output is not delayed
		0 = HFINTOSC output is delayed until oscillator is stable (IOFS = 1)
ENHCPU	CONFIG4L	Enhanced CPU Enable bit
		1 = Enhanced CPU enabled
		0 = Enhanced CPU disabled
BBSIZ	CONFIG4L	Boot Block Size Select bit
		1 = 2 kW Boot Block size for PIC18F14K22 (1 kW Boot Block size for
		PIC18F13K22)
		0 = 1 kW Boot Block size for PIC18F14K22 (512 W Boot Block size for PIC18F13K22)
LVP	CONFIG4L	Low-Voltage Programming Enable bit
		1 = Low-Voltage Programming enabled, RC3 is the PGM pin
		0 = Low-Voltage Programming disabled, RC3 is an I/O pin
STVREN	CONFIG4L	Stack Overflow/Underflow Reset Enable bit
		1 = Reset on stack overflow/underflow enabled
		0 = Reset on stack overflow/underflow disabled
CP1	CONFIG5L	Code Protection bits (Block 1 code memory area)
		1 = Block 1 is not code-protected
		0 = Block 1 is code-protected
CP0	CONFIG5L	Code Protection bits (Block 0 code memory area)
		1 = Block 0 is not code-protected
		0 = Block 0 is code-protected
CPD	CONFIG5H	Code Protection bits (Data EEPROM)
		1 = Data EEPROM is not code-protected

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TABLE 6-3: PIC18F1XK22/LF1XK22 BIT DESCRIPTIONS (CONTINUED)

Bit Name	Configuration Words	Description
СРВ	CONFIG5H	Code Protection bits (Boot Block memory area)
		1 = Boot Block is not code-protected0 = Boot Block is code-protected
WRT1	CONFIG6L	Write Protection bits (Block 1 code memory area)
		1 = Block 1 is not write-protected0 = Block 1 is write-protected
WRT0	CONFIG6L	Write Protection bits (Block 0 code memory area)
		1 = Block 0 is not write-protected0 = Block 0 is write-protected
WRTD	CONFIG6H	Write Protection bit (Data EEPROM)
		1 = Data EEPROM is not write-protected0 = Data EEPROM is write-protected
WRTB	CONFIG6H	Write Protection bit (Boot Block memory area)
		1 = Boot Block is not write-protected0 = Boot Block is write-protected
WRTC	CONFIG6H	Write Protection bit (Configuration registers)
		1 = Configuration registers are not write-protected0 = Configuration registers are write-protected
EBTR1	CONFIG7L	Table Read Protection bit (Block 1 code memory area)
		 1 = Block 1 is not protected from table reads executed in other blocks 0 = Block 1 is protected from table reads executed in other blocks
EBTR0	CONFIG7L	Table Read Protection bit (Block 0 code memory area)
		 1 = Block 0 is not protected from table reads executed in other blocks 0 = Block 0 is protected from table reads executed in other blocks
EBTRB	CONFIG7H	Table Read Protection bit (Boot Block memory area)
		 1 = Boot Block is not protected from table reads executed in other blocks 0 = Boot Block is protected from table reads executed in other blocks
DEV<10:3>	DEVID2	Device ID bits
		These bits are used with the DEV<2:0> bits in the DEVID1 register to identify part number.
DEV<2:0>	DEVID1	Device ID bits
		These bits are used with the DEV<10:3> bits in the DEVID2 register to identify part number.
REV<4:0>	DEVID1	Revision ID bits
		These bits are used to indicate the revision of the device.

7.0 EMBEDDING CONFIGURATION WORD INFORMATION IN THE HEX FILE

To allow portability of code, a PIC18F1XK22/LF1XK22 programmer is required to read the Configuration Word locations from the hex file. If Configuration Word information is not present in the hex file, then a simple warning message should be issued. Similarly, while saving a hex file, all Configuration Word information must be included. An option to not include the Configuration Word information may be provided. When embedding Configuration Word information in the hex file, it should start at address 300000h.

Microchip Technology Inc. feels strongly that this feature is important for the benefit of the end customer.

7.1 Embedding Data EEPROM Information In the HEX File

To allow portability of code, a PIC18F1XK22/LF1XK22 programmer is required to read the data EEPROM information from the hex file. If data EEPROM information is not present, a simple warning message should be issued. Similarly, when saving a hex file, all data EEPROM information must be included. An option to not include the data EEPROM information may be provided. When embedding data EEPROM information in the hex file, it should start at address F00000h.

Microchip Technology Inc. believes that this feature is important for the benefit of the end customer.

7.2 Checksum Computation

The checksum is calculated by summing the following:

- · The contents of all code memory locations
- · The Configuration Word, appropriately masked
- ID locations (Only if any portion of program memory is code-protected)

The Least Significant 16 bits of this sum are the checksum.

Code protection limits access to program memory by both external programmer (code-protect) and code execution (table read protect). The ID locations, when included in a code protected checksum, contain the checksum of an unprotected part. The unprotected checksum is distributed: one nibble per ID location. Each nibble is right justified.

Table 7-1 describes how to calculate the checksum for each device.

Note:

The checksum calculation differs depending on the code-protect setting. Since the code memory locations read out differently depending on the code-protect setting, the table describes how to manipulate the actual code memory values to simulate the values that would be read from a protected device. When calculating a checksum by reading a device, the entire code memory can simply be read and summed. The Configuration Word and ID locations can always be read.

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TABLE 7-1: CHECKSUM COMPUTATION

Device	Code-Protect BBSIZ = 0	Checksum	Blank Value	0xAA at 0 and Max Address
	None	SUM[0000:01FFF]+SUM[2000:3FFF]+ (CONFIG1L & 00h)+(CONFIG1H & FFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 88h)+ (CONFIG4L & CDh)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)	C35Bh	C2B1h
PIC18F14K22/ PIC18LF14K22	Boot Block	SUM[0800:1FFF]+SUM[2000:3FFF]+ (CONFIG1L & 00h)+(CONFIG1H & FFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+ (CONFIG3H & 88h)+ (CONFIG4L & CDh)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	CB3Ah	CAE0h
11010L1141(22	Boot/ Block 0	SUM[2000:3FFF]+ (CONFIG1L & 00h)+(CONFIG1H & FFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 88h)+ (CONFIG4L & CDh)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	E537h	E2DFh
	All	(CONFIG1L & 00h)+(CONFIG1H & FFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 88h)+ (CONFIG4L & CDh)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	0337h	0332h
	None	SUM[0000:0FFF]+SUM[1000:1FFF]+ (CONFIG1L & 00h)+(CONFIG1H & FFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 88h)+ (CONFIG4L & CDh)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)	E35Bh	E2B1h
PIC18F13K22/ PIC18LF13K22	Boot Block	SUM[0400:0FFF]+SUM[1000:1FFF]+ (CONFIG1L & 00h)+(CONFIG1H & FFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+ (CONFIG3H & 88h)+ (CONFIG4L & CDh)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	E73Ch	E6E2h
PIC18LF13K22	Boot/ Block 0	SUM[1000:1FFF]+ (CONFIG1L & 00h)+(CONFIG1H & FFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 88h)+ (CONFIG4L & CDh)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	F539h	F2E1h
	All	(CONFIG1L & 00h)+(CONFIG1H & FFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 88h)+ (CONFIG4L & CDh)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	0339h	0334h

 Legend:
 Item
 Description

CONFIGx = Configuration Word

SUM[a:b] = Sum of locations, a to b inclusive

SUM_ID = Byte-wise sum of lower four bits of all customer ID locations

+ = Addition & = Bit-wise AND

8.0 AC/DC CHARACTERISTICS TIMING REQUIREMENTS FOR PROGRAM/ VERIFY TEST MODE

Standard Operating Conditions

Operating Temperature: 25°C is recommended

Operati	ing Temp	erature: 25°C is recommended				
Param No.	Sym.	Characteristic	Min.	Max.	Units	Conditions
D110	VIHH	High-Voltage Programming Voltage on MCLR/Vpp/RA3	8	9	V	
D110A	VIHL	Low-Voltage Programming Voltage on MCLR/VPP/RA3	1.80	VDD	V	
D111	VDD	PIC18F1XK22 (includes Bulk Erase)	2.70	5.50	V	
		PIC18LF1XK22 (includes Bulk Erase)	2.70	3.60	V	
D112	IPP	Programming Current on MCLR/VPP/RA3	_	5	mA	
D113	IDDP	Supply Current During Programming	_	5	mA	
D031	VIL	Input Low Voltage	Vss	0.2 VDD	V	
D041	VIH	Input High Voltage	0.8 VDD	VDD	V	
D080	Vol	Output Low Voltage	_	0.6	V	IOL = 3.0 mA @ 2.7V
D090	Vон	Output High Voltage	VDD - 0.7	_	V	IOH = -2.0 mA @ 2.7V
D012	Сю	Capacitive Loading on I/O pin (PGD)	_	50	pF	To meet AC specifications
P1	TR	MCLR/VPP/RA3 Rise Time to enter Program/Verify mode	_	1.0	μS	(Note 1)
P2	TPGC	Serial Clock (PGC) Period	100	_	ns	VDD = 3.6V
			1	_	μS	VDD = 1.8V
P2A	TPGCL	Serial Clock (PGC) Low Time	40	_	ns	VDD = 3.6V
			400	_	ns	VDD = 1.8V
P2B	TPGCH	Serial Clock (PGC) High Time	40	_	ns	VDD = 3.6V
			400	_	ns	VDD = 1.8V
P3	TSET1	Input Data Setup Time to Serial Clock ↓	15	_	ns	
P4	THLD1	Input Data Hold Time from PGC ↓	15	_	ns	
P5	TDLY1	Delay between 4-bit Command and Command Operand	40	_	ns	
P5A	TDLY1A	Delay between 4-bit Command Operand and next 4-bit Command	40	_	ns	
P6	TDLY2	Delay between Last PGC ↓ of Command Byte to First PGC ↑ of Read of Data Word	20	_	ns	
P9	TDLY5	PGC High Time (minimum programming time)	1	_	ms	Externally Timed
P9A	TDLY5A	PGC High Time	5		ms	Configuration Word programming time
P10	TDLY6	PGC Low Time after Programming (high-voltage discharge time)	100	_	μS	
P11	TDLY7	Delay to allow Self-Timed Data Write or Bulk Erase to occur	5	_	ms	
P11A	TDRWT	Data Write Polling Time	4	_	ms	

Note 1: Do not allow excess time when transitioning MCLR between VIL and VIHH; this can cause spurious program executions to occur. The maximum transition time is:

¹ Tcy + TpwRT (if enabled) + 1024 Tosc (for LP, HS, HS/PLL and XT modes only) + 2 ms (for HS/PLL mode only) + 1.5 μ s (for EC mode only) where Tcy is the instruction cycle time, TpwRT is the Power-up Timer period and Tosc is the oscillator period. For specific values, refer to the Electrical Characteristics section of the device data sheet for the particular device.

MCLR/VPP/RA3 ↓ to VDD ↓

MCLR/VPP/RA3 ↓ to PGM ↓

Hold time after VPP changes

Delay from PGC ↑ to PGD High-Z

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P17

P18

P19

P20

THLD3

THLD4

TPPDP

THIZ

8.0 AC/DC CHARACTERISTICS TIMING REQUIREMENTS FOR PROGRAM/ VERIFY TEST MODE (CONTINUED)

Standard Operating Conditions Operating Temperature: 25°C is recommended **Param** Sym. Characteristic Min. Max. Units Conditions No. Input Data Hold Time from MCLR/VPP/RA3 ↑ P12 THLD2 2 μS Input Data Hold Time from MCLR/VPP/RA3 ↑ P12A THLD2A 70 μS PIC18F1XK22 Only. Refer to Figure 2.1.1. VDD ↑ Setup Time to MCLR/VPP/RA3 ↑ P13 TSET2 100 ns TSET2A VDD ↑ Setup Time to MCLR/VPP/RA3 ↑ PIC18F1XK22 Only. P13A 70 μS Refer to Figure 2.1.1. P14 Data Out Valid from PGC ↑ **TVALID** 10 ns PGM ↑ Setup Time to MCLR/VPP/RA3 ↑ 2 P15 TSET3 μS Delay between Last PGC ↓ and MCLR/VPP/RA3 ↓ P16 TDLY8 0 s

0

3

5

100

10

ns

s

nS

μS

Note 1: Do not allow excess time when transitioning MCLR between VIL and VIHH; this can cause spurious program executions to occur. The maximum transition time is:

¹ TCY + TPWRT (if enabled) + 1024 TOSC (for LP, HS, HS/PLL and XT modes only) + 2 ms (for HS/PLL mode only) + 1.5 μ s (for EC mode only) where TCY is the instruction cycle time, TPWRT is the Power-up Timer period and TOSC is the oscillator period. For specific values, refer to the Electrical Characteristics section of the device data sheet for the particular device.

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